PE82H2G

N-Channel Enhancement Mode Power MOSFET

Description

The PE82H2G uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. It can be used in a wide variety of applications. It is ESD protected.

General Features

- V_{DS} = 18V, I_D = 120A
  $R_{DS(ON)}$ < 2.1mΩ @ V_{GS}=4.5V
  $R_{DS(ON)}$ < 2.5mΩ @ V_{GS}=2.5V
  ESD Rating: 4000V HBM
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- Battery management
- PWM
- Load switch
- Uninterruptible power supply

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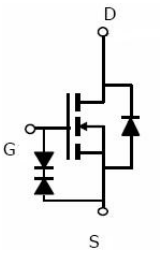
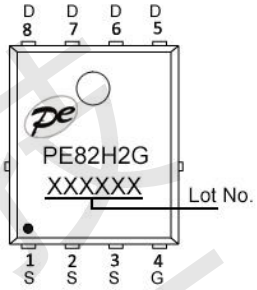
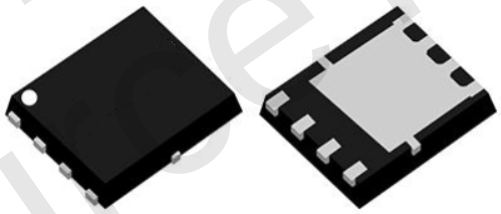


Schematic diagram



Marking and pin assignment



DFN5x6-8L

Absolute Maximum Ratings (TC=25℃ unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	18	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D	120	A
Drain Current-Continuous (T_C=100℃)		91	A
Pulsed Drain Current (Note 1)	I_{DM}	400	A
Maximum Power Dissipation	P_D	83	W
Avalanche Energy (L=0.5mH)	E_{AS}	333	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	1.5	℃/W

PE82H2G

Electrical Characteristics (TC=25℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_D=250μA	-	18	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=16V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±10V,V_{DS}=0V	-	-	±8	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	0.45	0.7	1	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=4.5V,I_D=20A	-	1.6	2.1	mΩ
		V_{GS}=2.5V,I_D=10A	-	2.3	2.5	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=20A	-	100	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	V_{DS}=10V,V_{GS}=0V, F=1.0MHz	-	4900	-	pF
Output Capacitance	C_{oss}		-	1200	-	pF
Reverse Transfer Capacitance (Note 4)	C_{rss}		-	1080	-	pF
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=10V,I_D=2A,R_L=1Ω, V_{GS}=4.5V,R_G=3Ω	-	12	-	nS
Turn-on Rise Time	t_r		-	11	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	48	-	nS
Turn-Off Fall Time	t_f		-	23	-	nS
Total Gate Charge	Q_g	V_{DS}=10V,I_D=25A, V_{GS}=4.5V	-	35	-	nC
Gate-Source Charge	Q_{gs}		-	9	-	nC
Gate-Drain Charge	Q_{gd}		-	18	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=1A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	120	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to product.

Typical Electrical and Thermal Characteristics

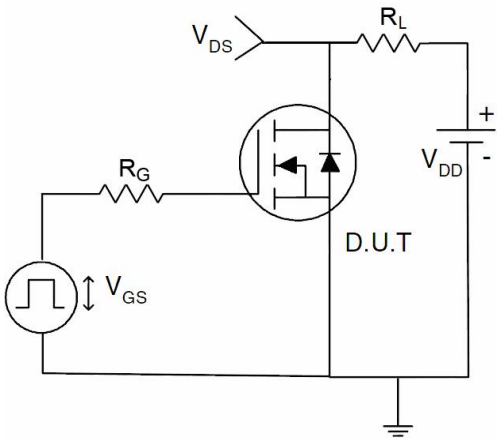


Figure 1 Switching Test Circuit

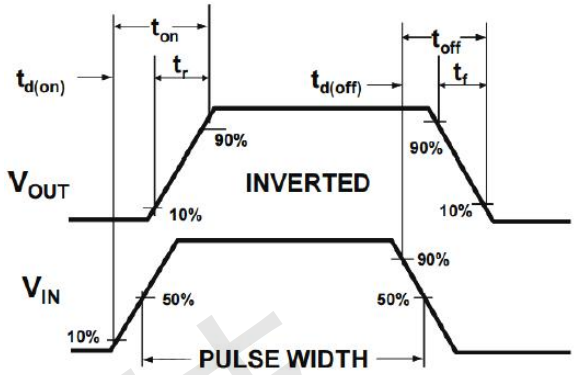


Figure 2 Switching Waveform

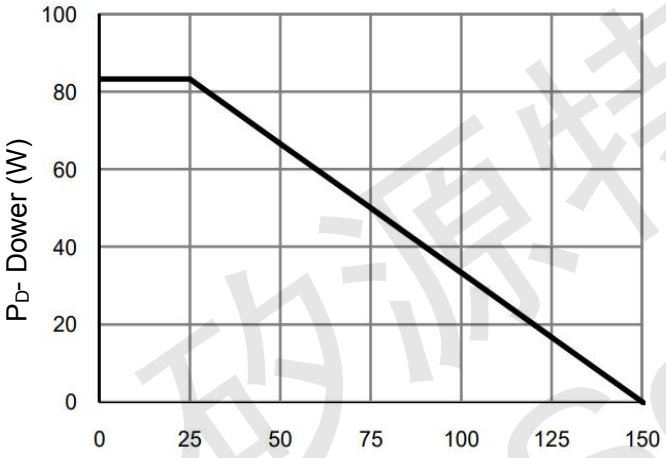


Figure 3 Power De-rating

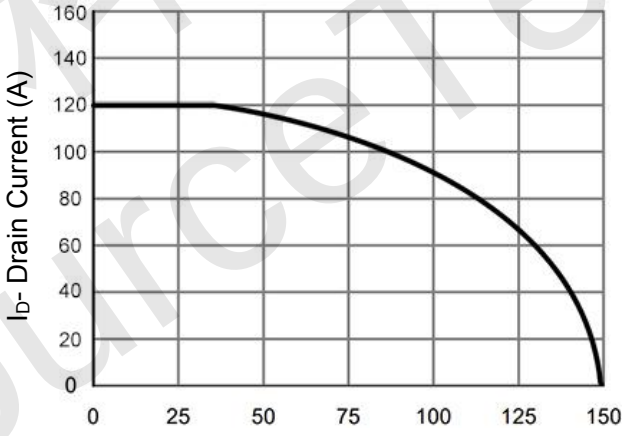


Figure 4 Drain Current

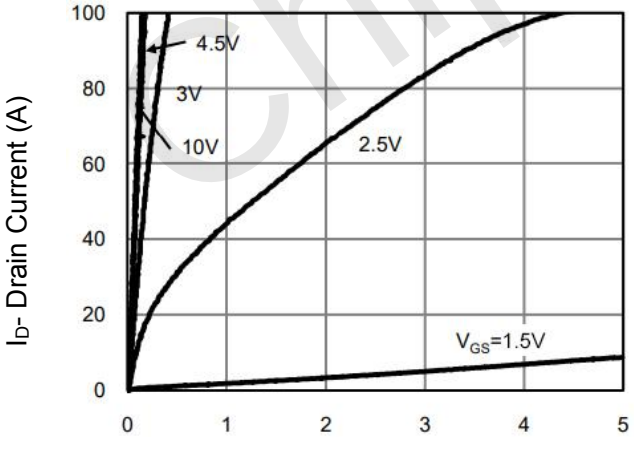


Figure 5 Output Characteristics

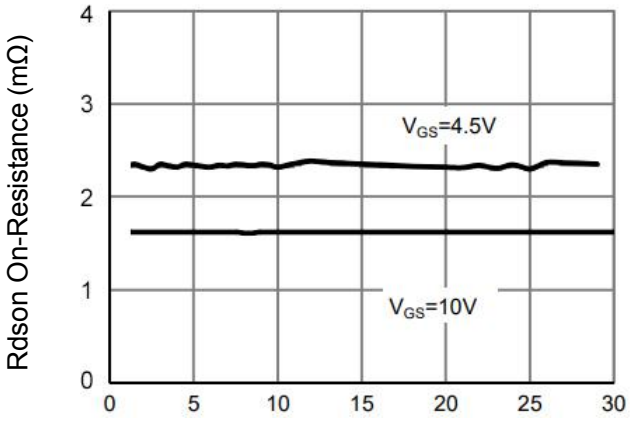


Figure 6 Rdson vs Drain Current

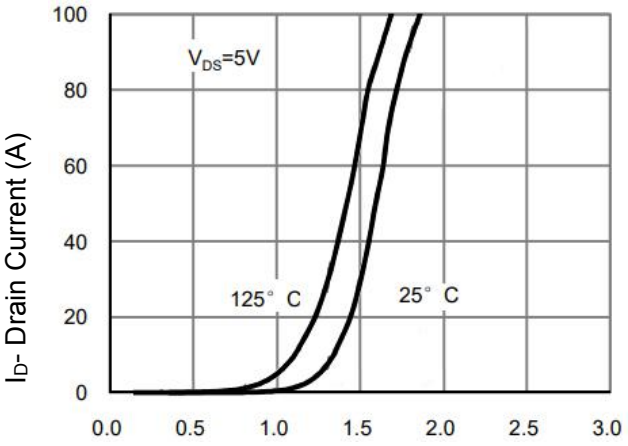


Figure 7 Transfer Characteristics

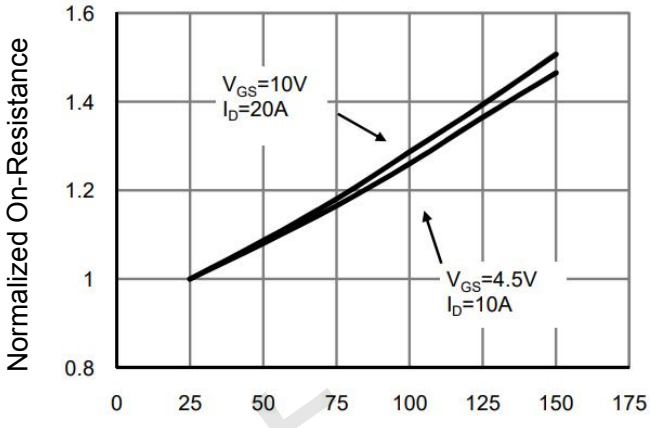


Figure 8 Rdson vs Junction Temperature

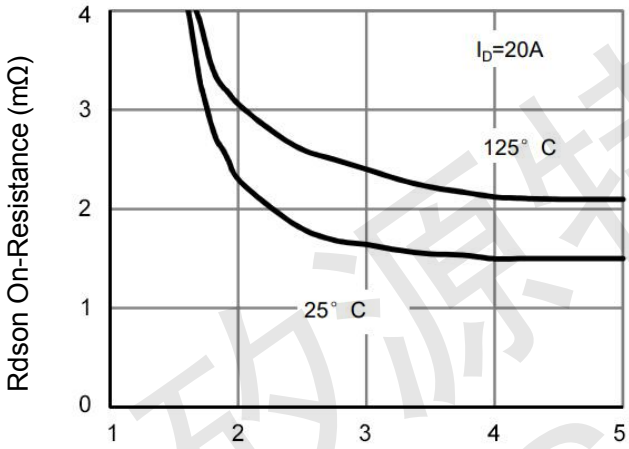


Figure 9 Rdson vs Vgs

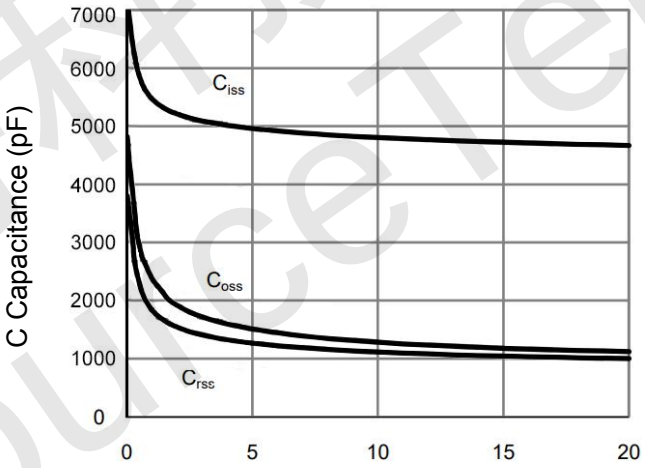


Figure 10 Capacitance vs Vds

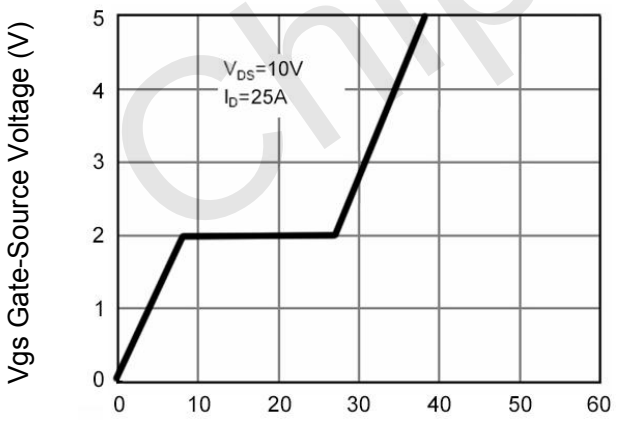


Figure 11 Gate Charge

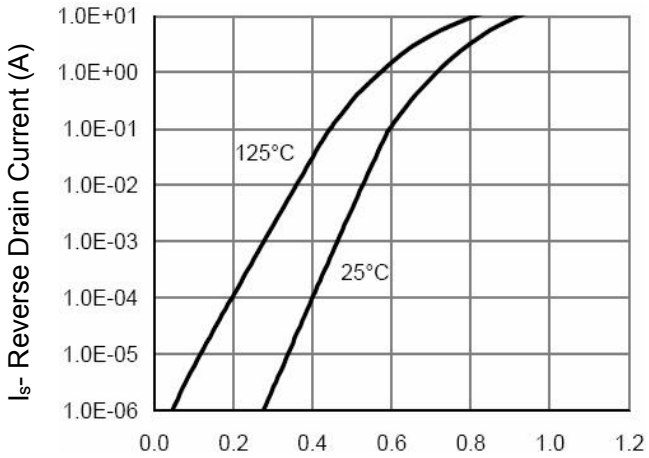


Figure 12 Source- Drain Diode Forward

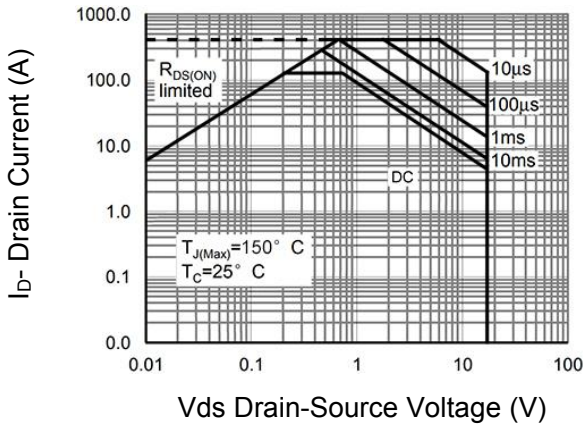


Figure 13 Safe Operation Area

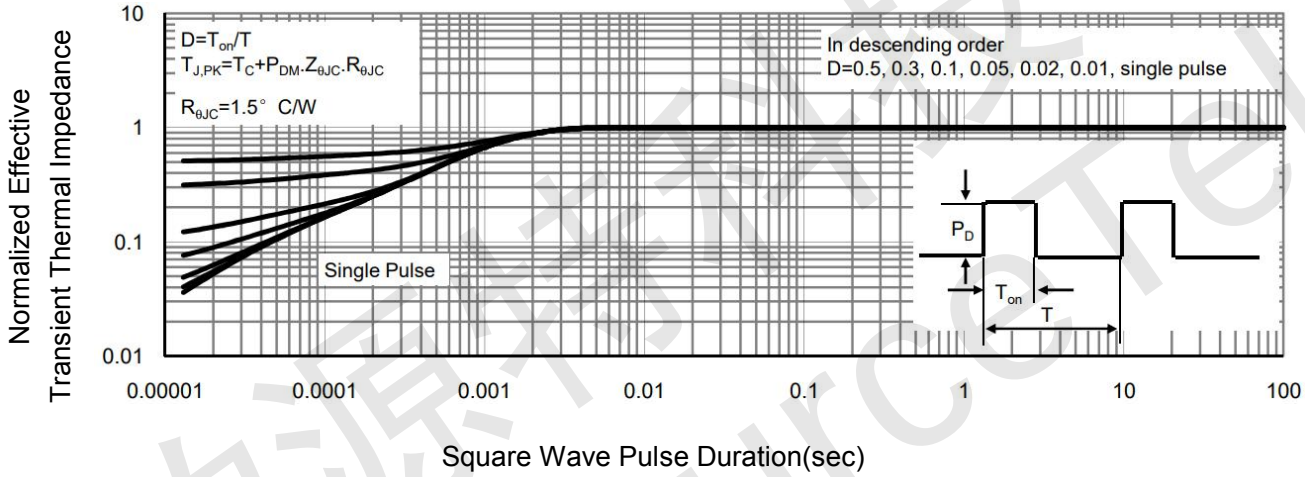
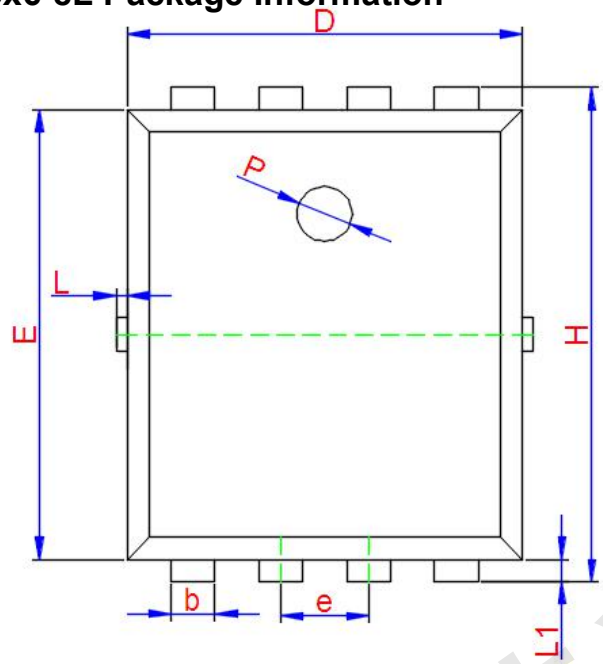
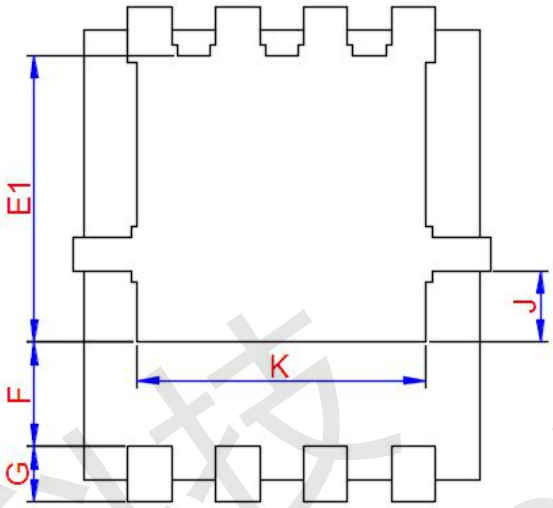
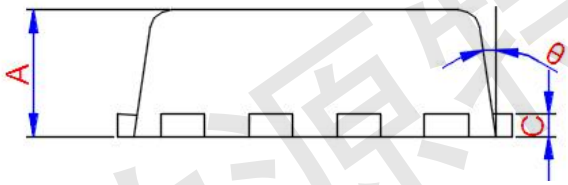


Figure 14 Normalized Maximum Transient Thermal Impedance

DFN5x6-8L Package Information







Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	0.800	0.900	1.000
b	0.350	0.420	0.490
c		0.254TYP.	
D	4.900	5.000	5.100
e		1.270TYP.	
E	5.700	5.800	5.900
E1		3.400TYP.	
F		1.400TYP.	
G		0.600TYP.	
H	5.950	6.080	6.200
J		0.950TYP.	
K		4.000TYP	
L	-	-	0.150
L1	0.100	0.140	0.180
P		1.000TYP.	
θ	6°	10°	14°